

FIG. 1  
Prior Art

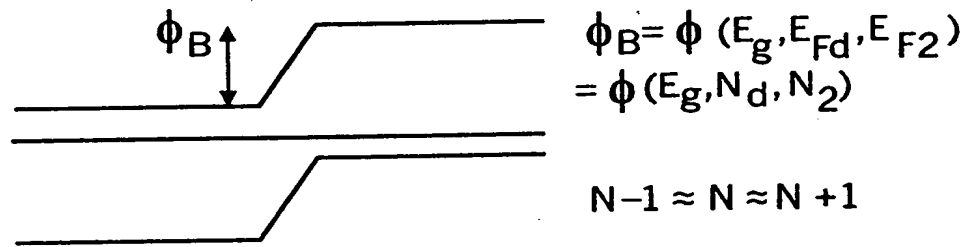


FIG. 5

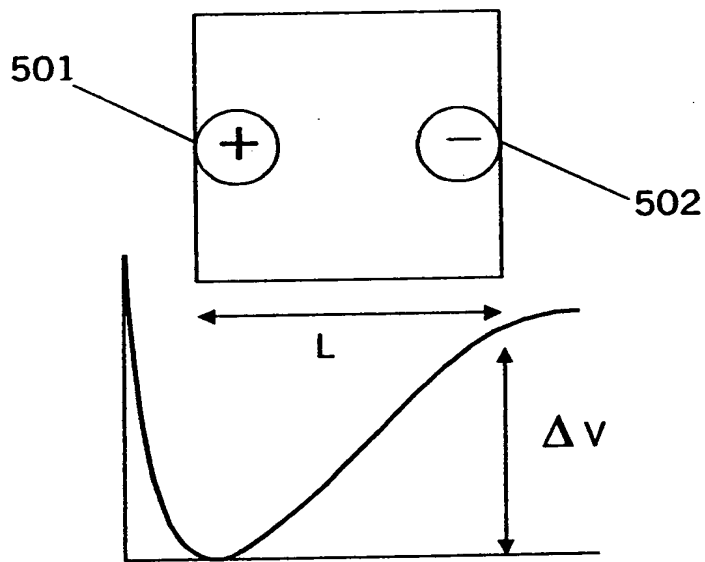


FIG. 14

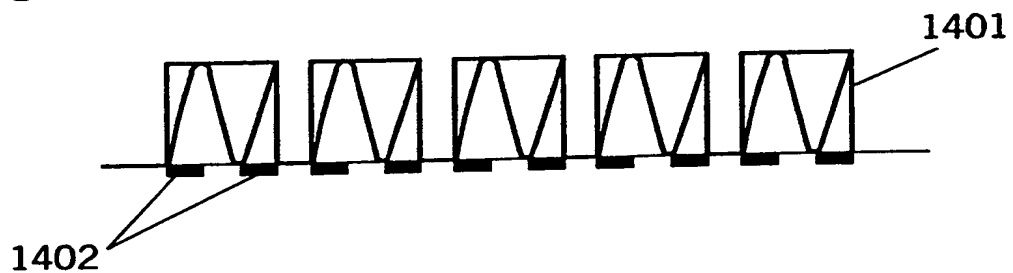


FIG. 2

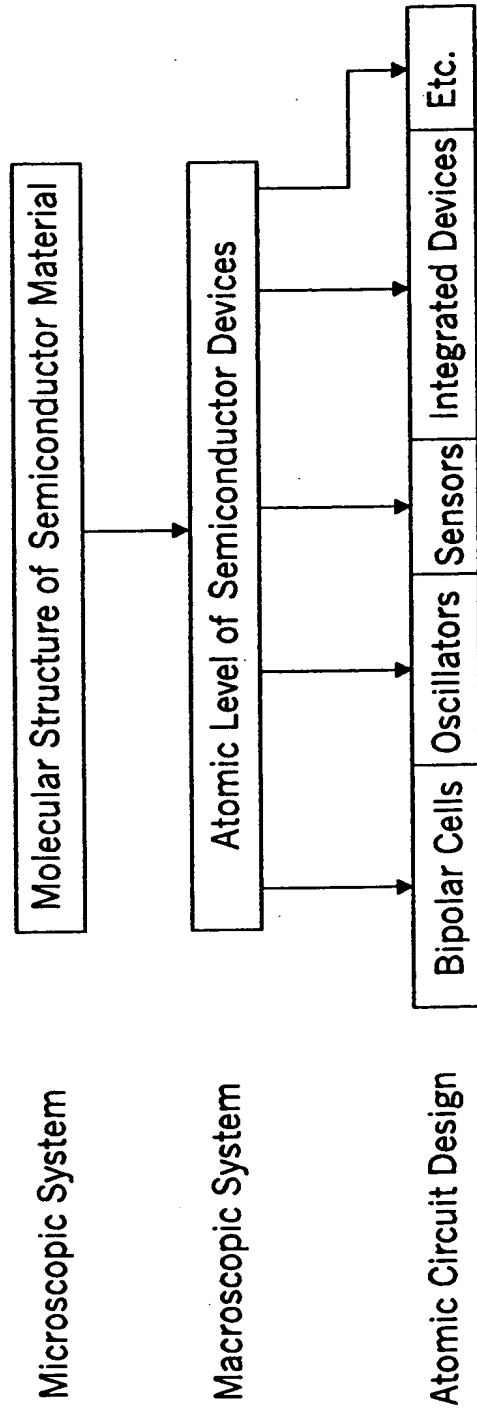


FIG. 3

L,nm	Number of Si atoms	Single-dopant concentration, cm <sup>-3</sup>	Equivalent resistivity, Ω-cm
100	50,000,000	1E+15	5.00
50	6,250,000	8E+15	2.00
10	50,000	1E+18	0.04
5	6,250	8E+18	0.01

FIG. 4

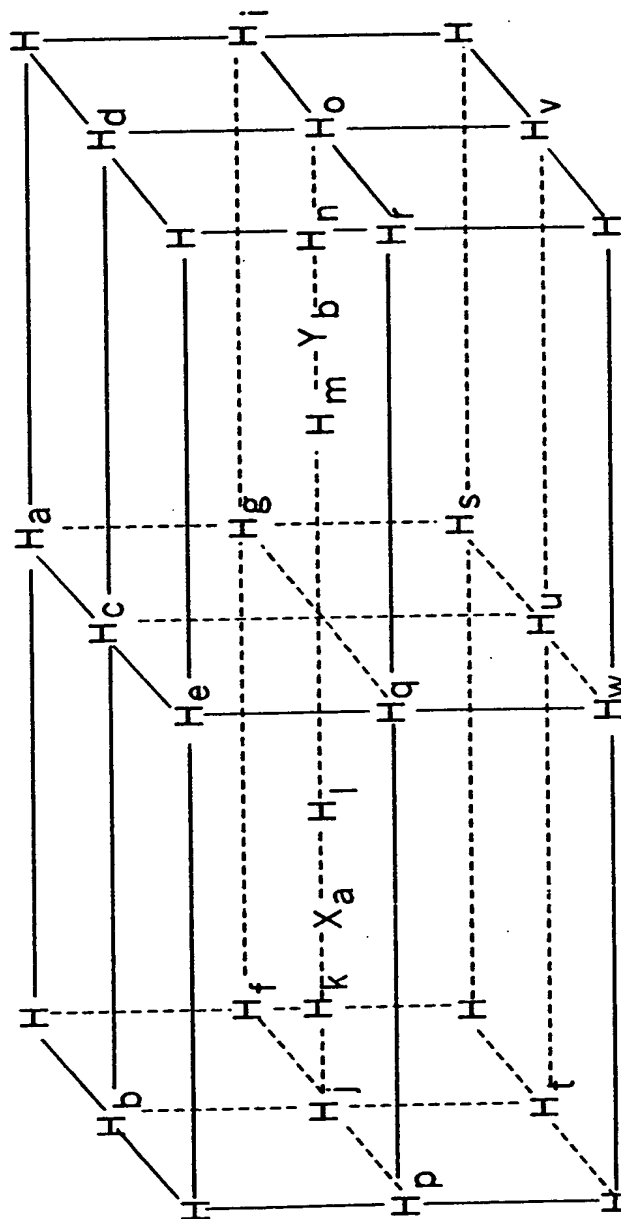


FIG. 6

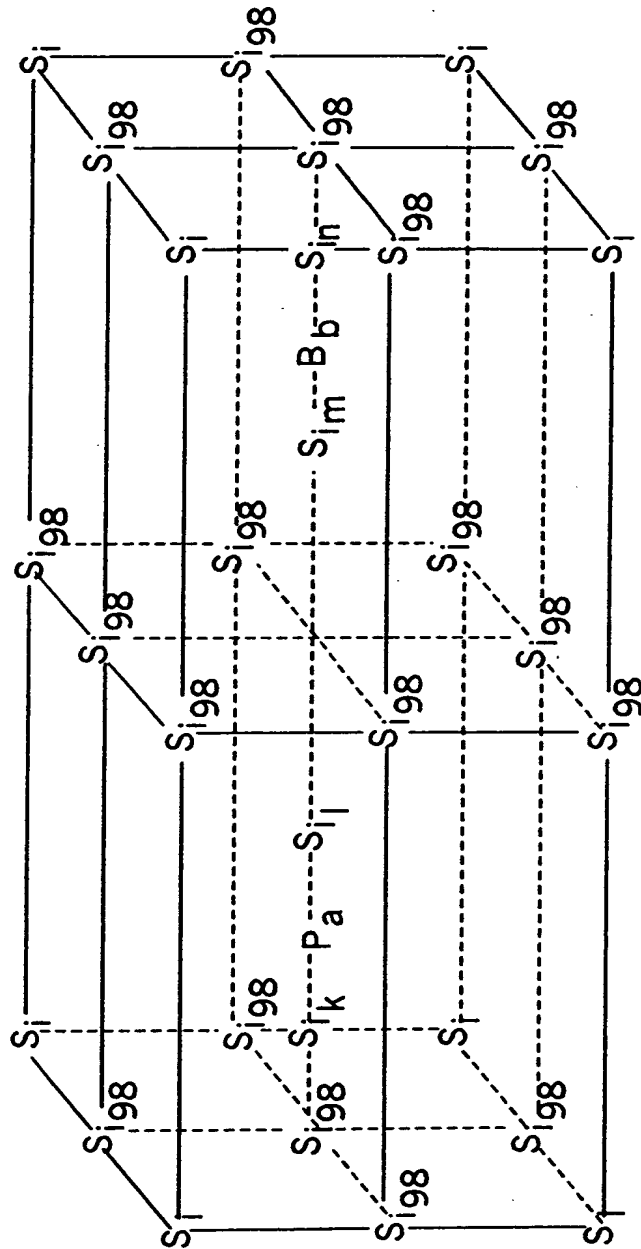
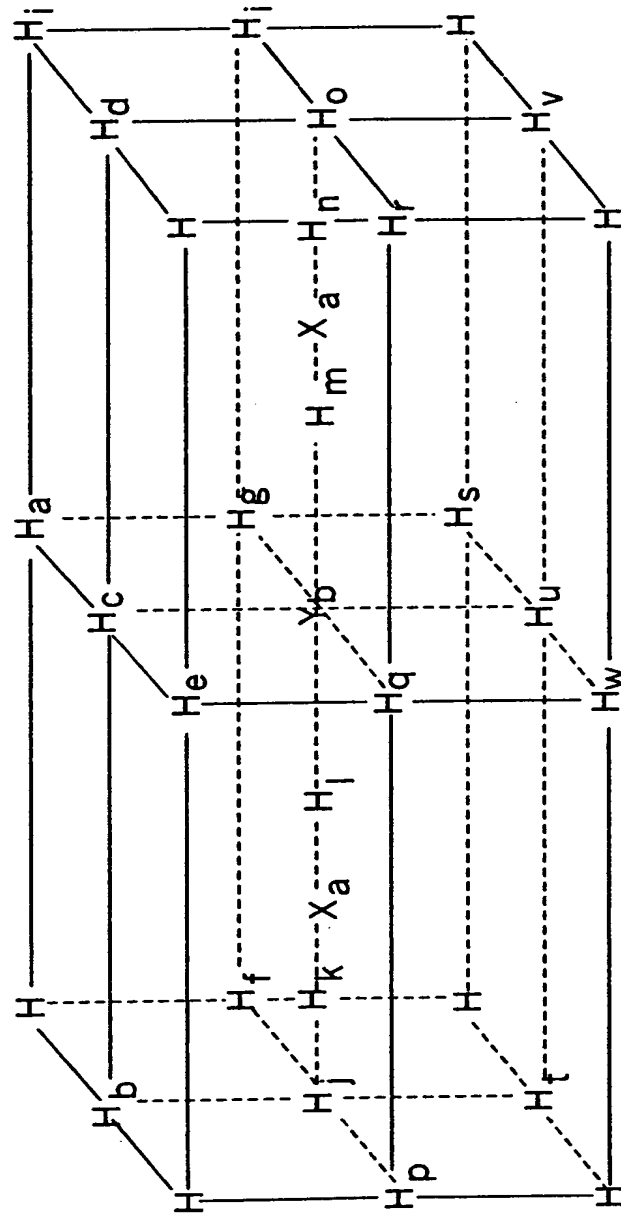


FIG. 7



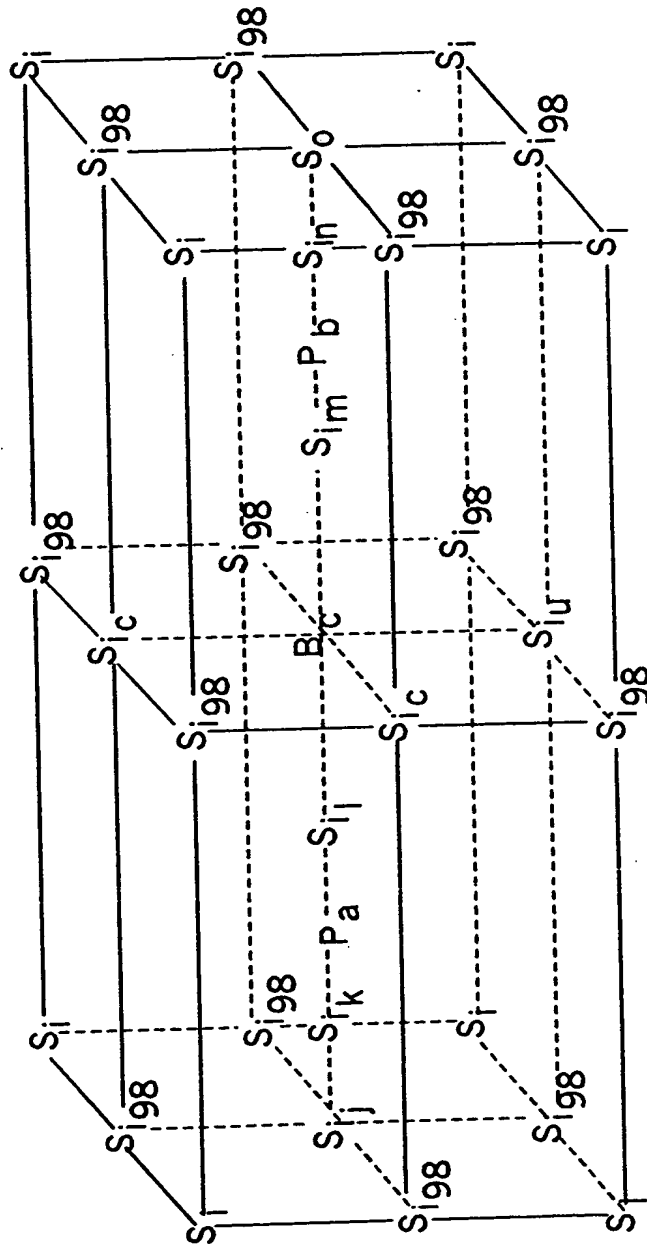


FIG. 9

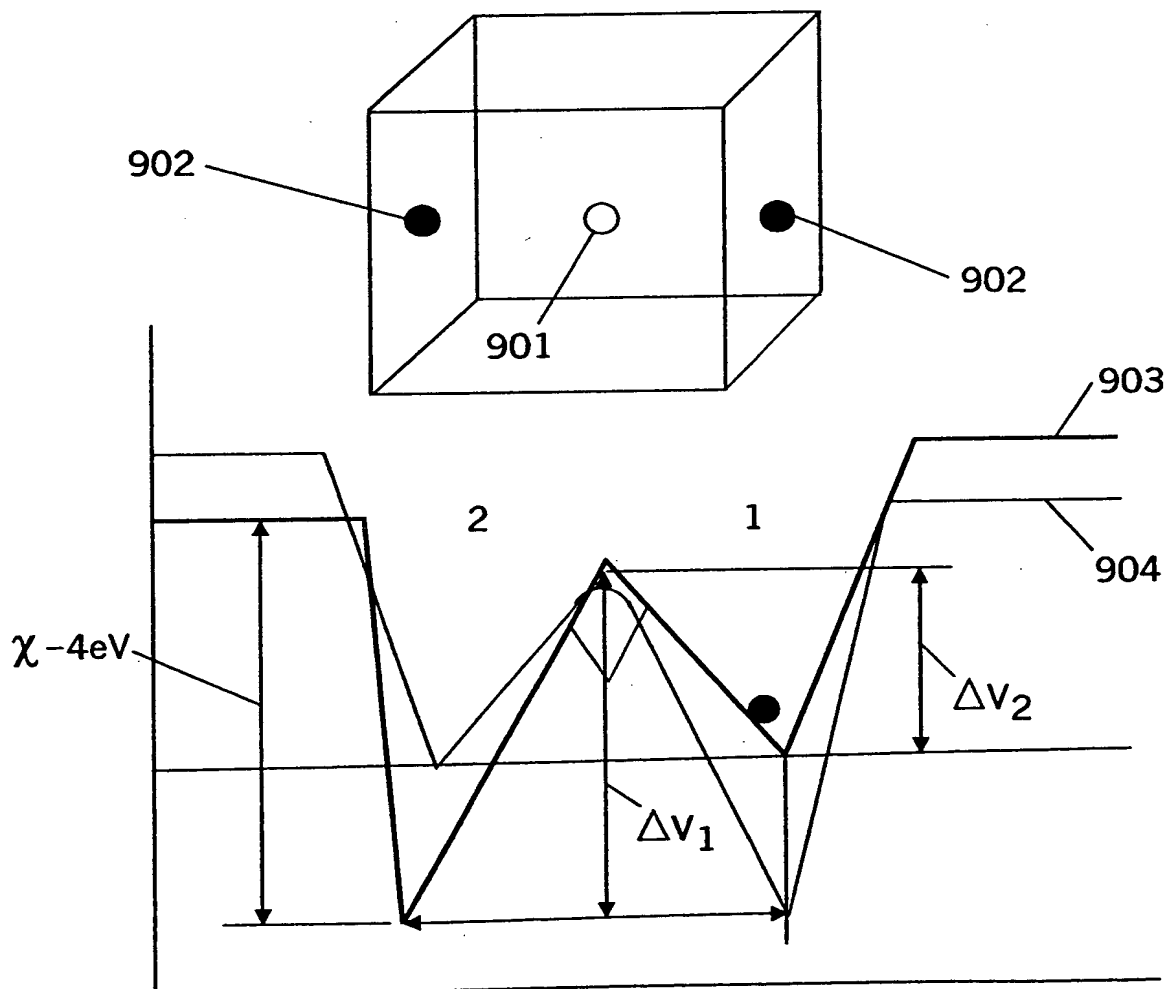


FIG. 10

$$\Delta V_1 = (e/\pi\epsilon_0\epsilon)L^{-1}$$

$$\Delta V_2 = (e/2\pi\epsilon_0\epsilon)L^{-1}$$

$$\Delta V_2 = \frac{1}{2} \Delta V_1$$

$$kT_{th} \sim \Delta V_2$$

$$T_{th} \sim \Delta V_2/k$$

– Thermal Threshold

L, nm	$\Delta V_1$ Volts	$\Delta V_2$ Volts	$T_{th}, K$
100	0.012	0.006	50
50	0.023	0.012	100
40	0.030	0.015	150
30	0.040	0.020	200
20	0.060	0.030	300
10	0.120	0.060	600
5	0.230	0.120	1200



FIG. 11

L, nm	$\Delta V_1$ Volts	$\Delta V_2$ Volts	$T_{th}, K$	$\tau, S$	f, GHz	Power/cell, W	Power/cm <sup>2</sup> , W/cm <sup>2</sup>	Power/1D-array W/cm
100	0.012	0.006	50	3.14E-10	3.18	5.86E-12	0.0586	2.93E-07
50	0.023	0.012	100	1.11E-10	8.99	3.31E-11	1.33	3.31E-06
40	0.03	0.015	150	7.96E-11	12.6	5.79E-11	3.62	7.24E-06
30	0.04	0.020	200	5.17E-11	19.4	1.19E-10	13.2	1.98E-05
20	0.06	0.030	300	2.81E-11	35.6	3.28E-10	81.9	8.19E-05
10	0.12	0.060	600	9.94E-12	101	1.85E-09	1850.0	9.26E-04
5	0.23	0.120	1200	3.52E-12	284	1.05E-08	41900.0	1.05E-02

FIG. 12

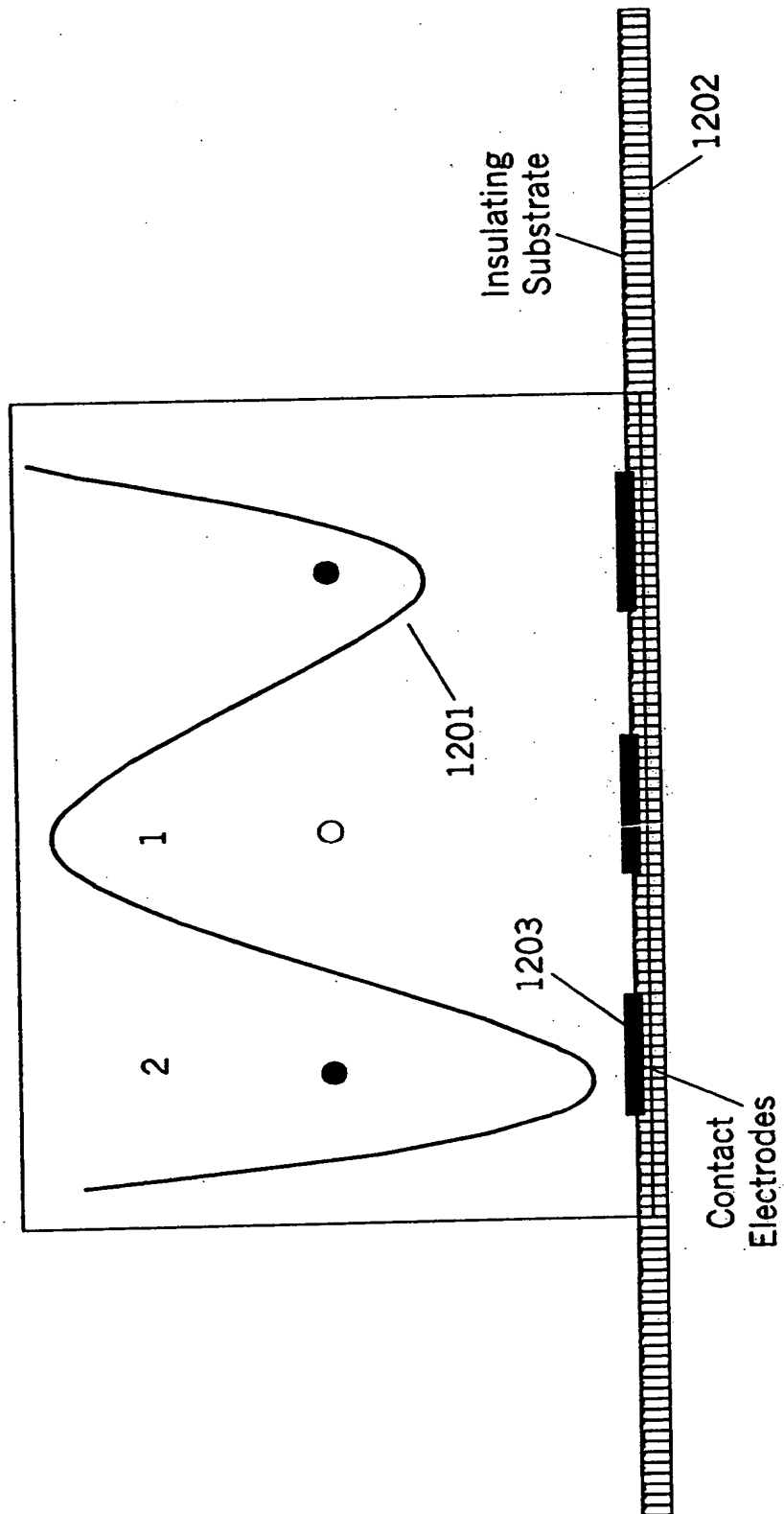


FIG. 13

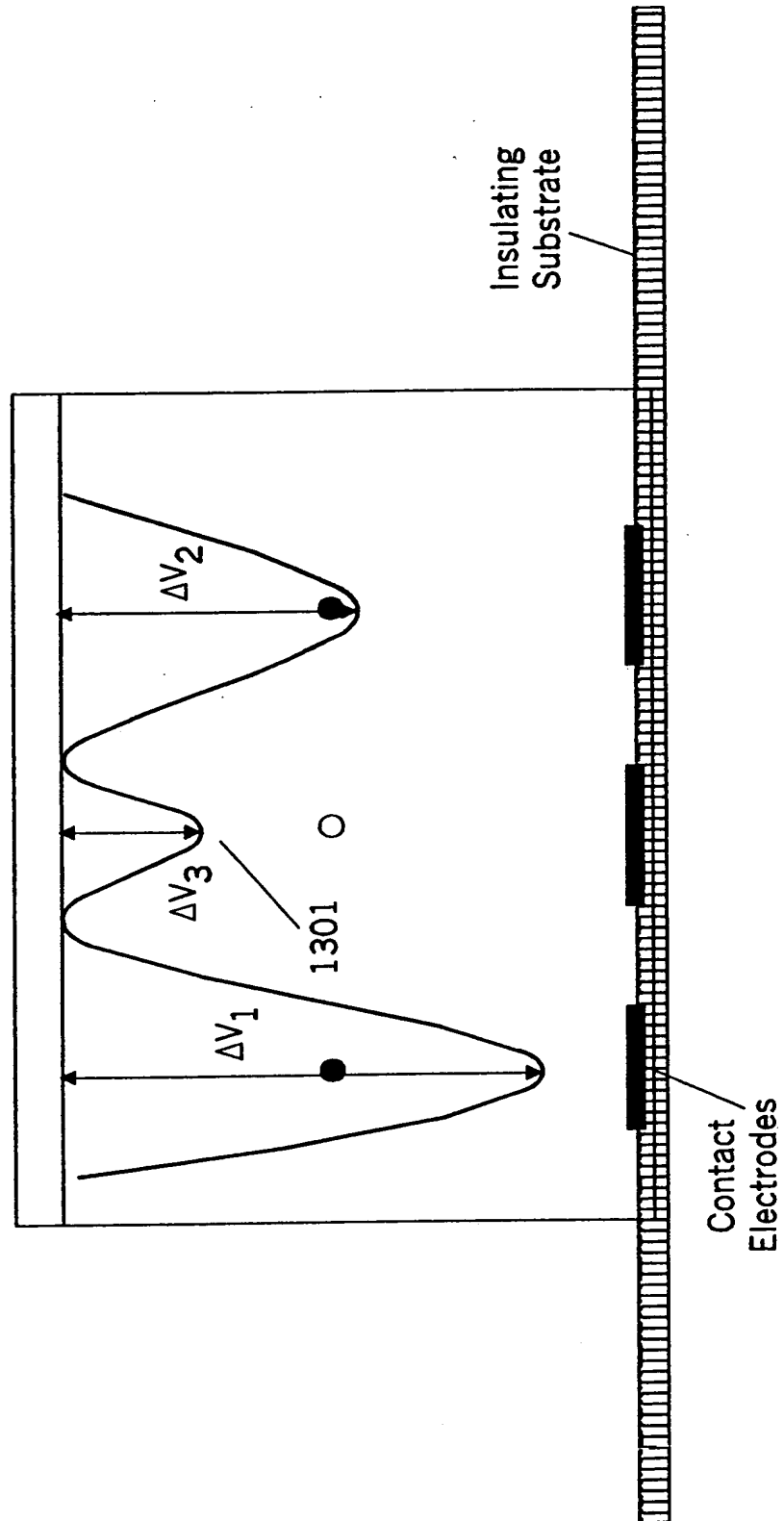


FIG. 15

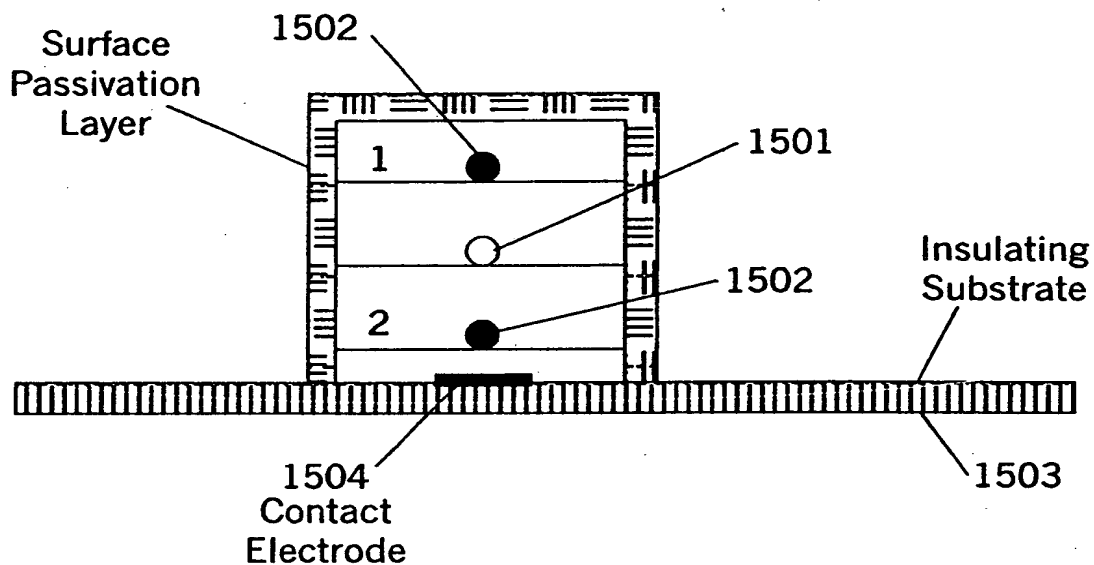
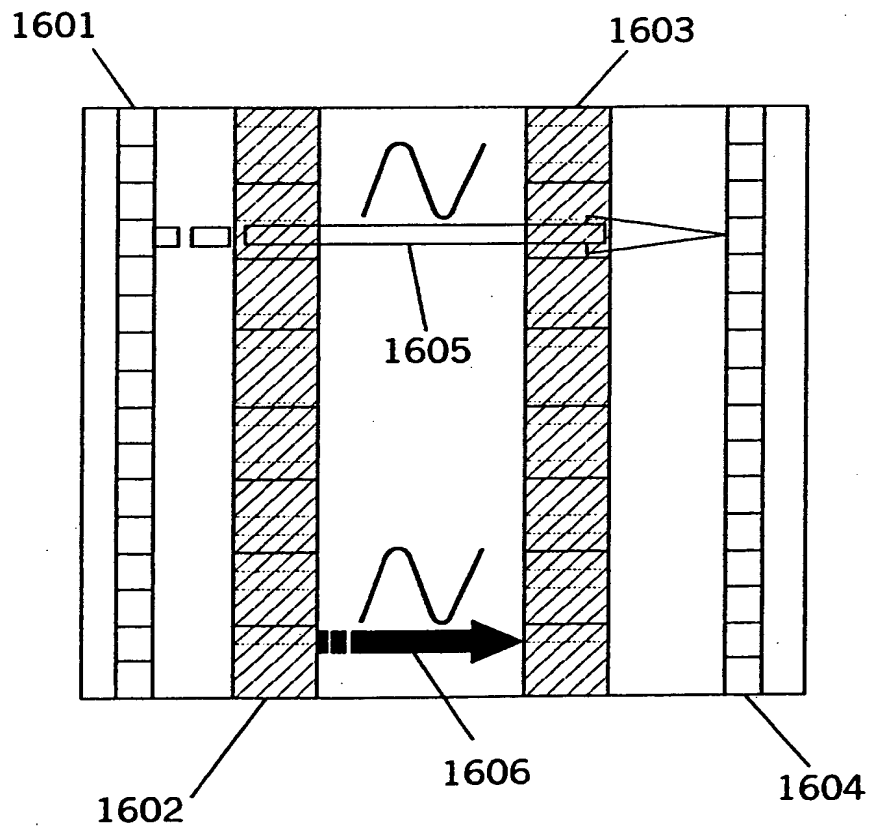


FIG. 16



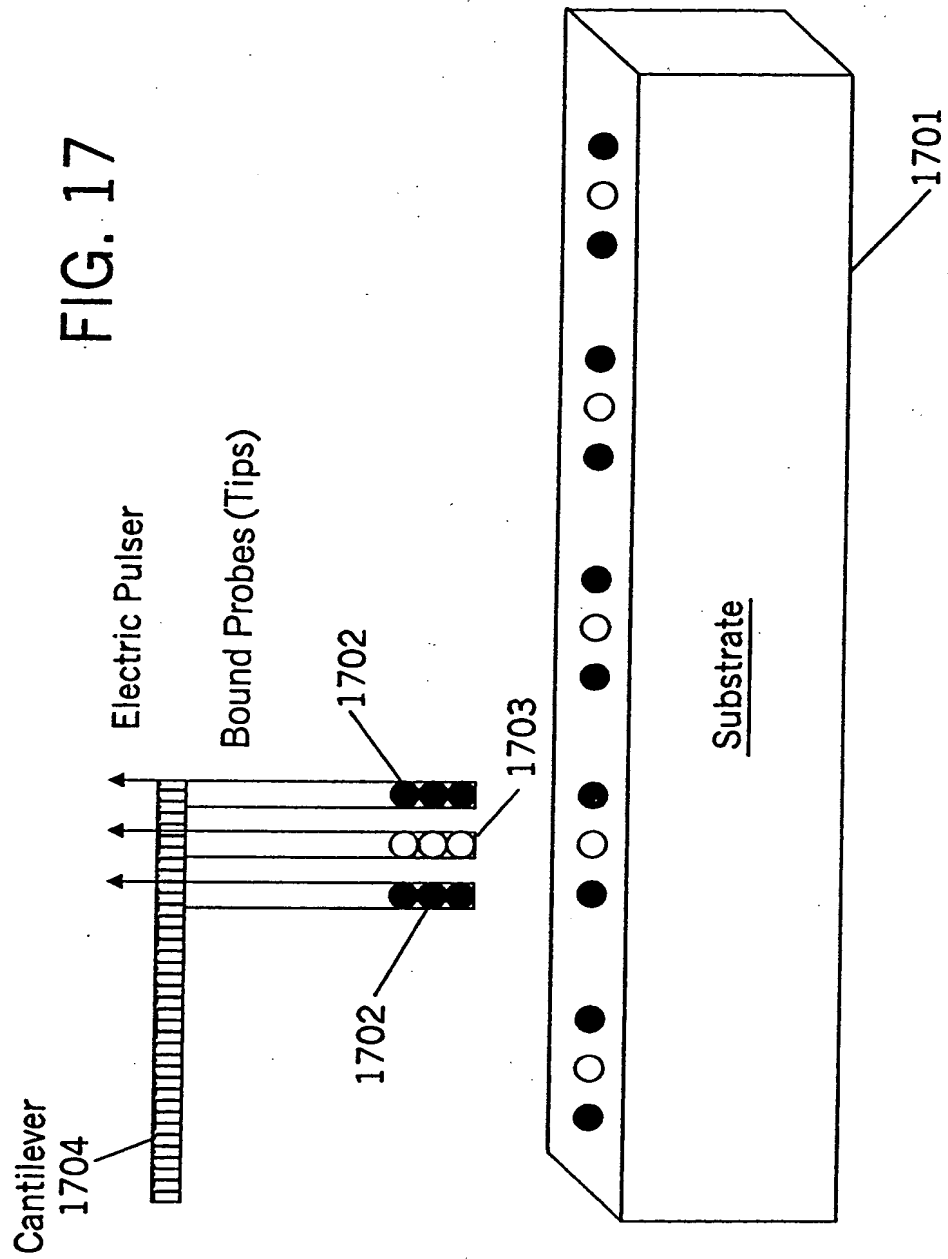


FIG. 18A

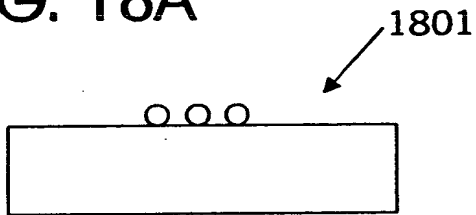


FIG. 18B

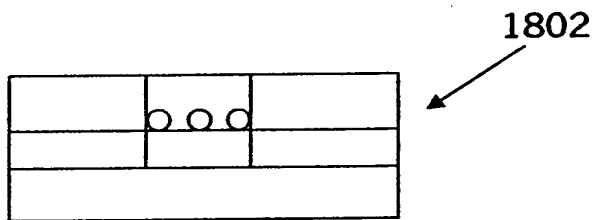


FIG. 18C

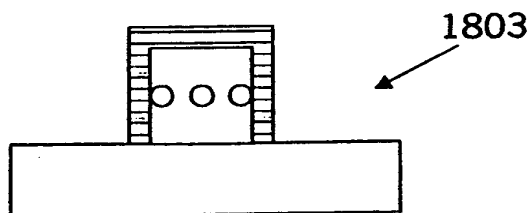


FIG. 19A



FIG. 19B

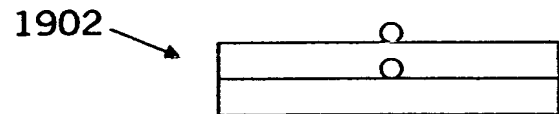


FIG. 19C

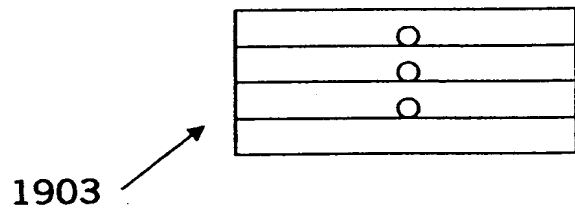


FIG. 19D

